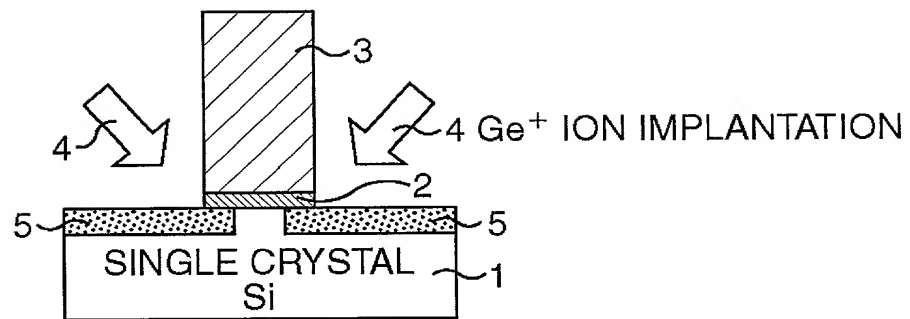
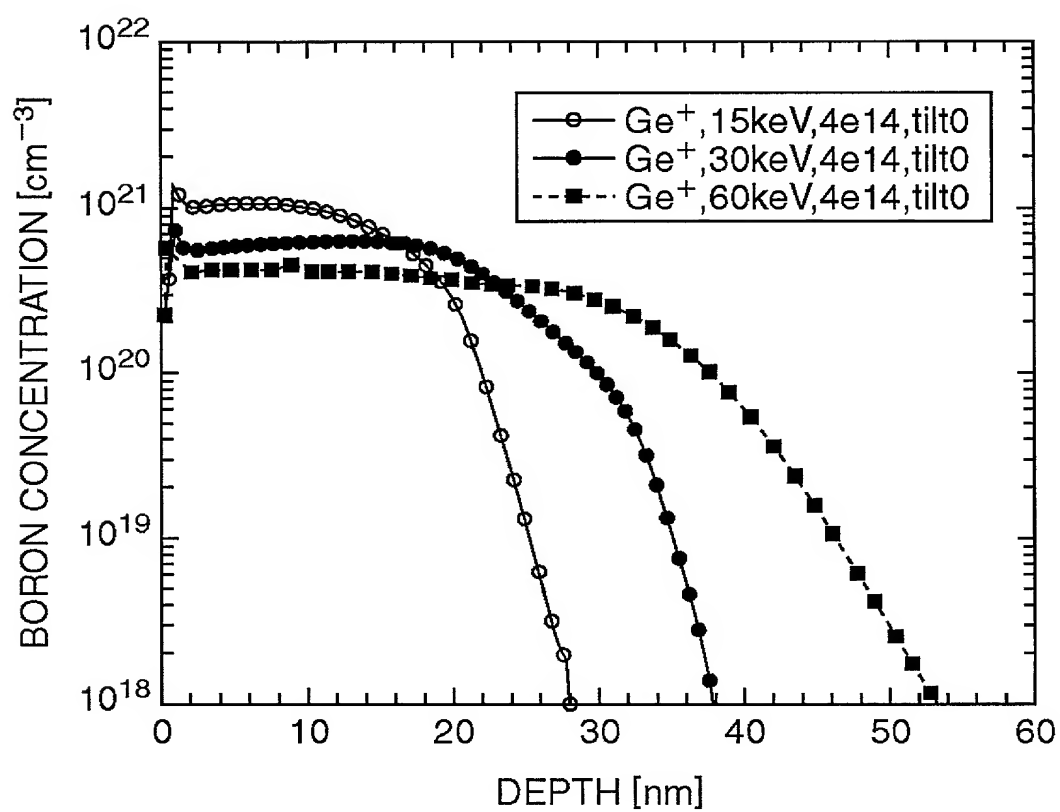


FIG. 1



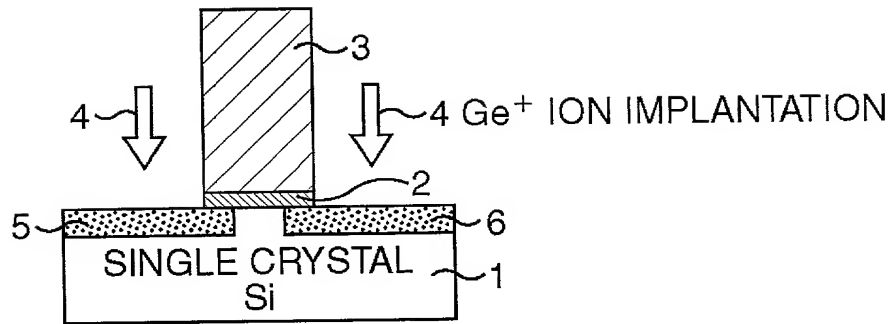
PARTS UNDER GATE ELECTRODE ALSO AMORPHOUSIZED
BY OBLIQUE AMORPHOUSIZING IMPLANTATION
(IMPURITIES IN THESE PARTS ACTIVATED)

FIG. 2



SECONDARY ION MASS SPECTROMETRY

FIG. 3



SOURCE/DRAINS HAVING PARTS UNDER GATE ELECTRODE ALSO AMORPHOUSIZED FORMED BY CONTROLLING ION IMPLANTATION CONDITION AND LASER IRRADIATION CONDITION (IMPURITIES IN THESE PARTS ACTIVATED)

FIG. 4

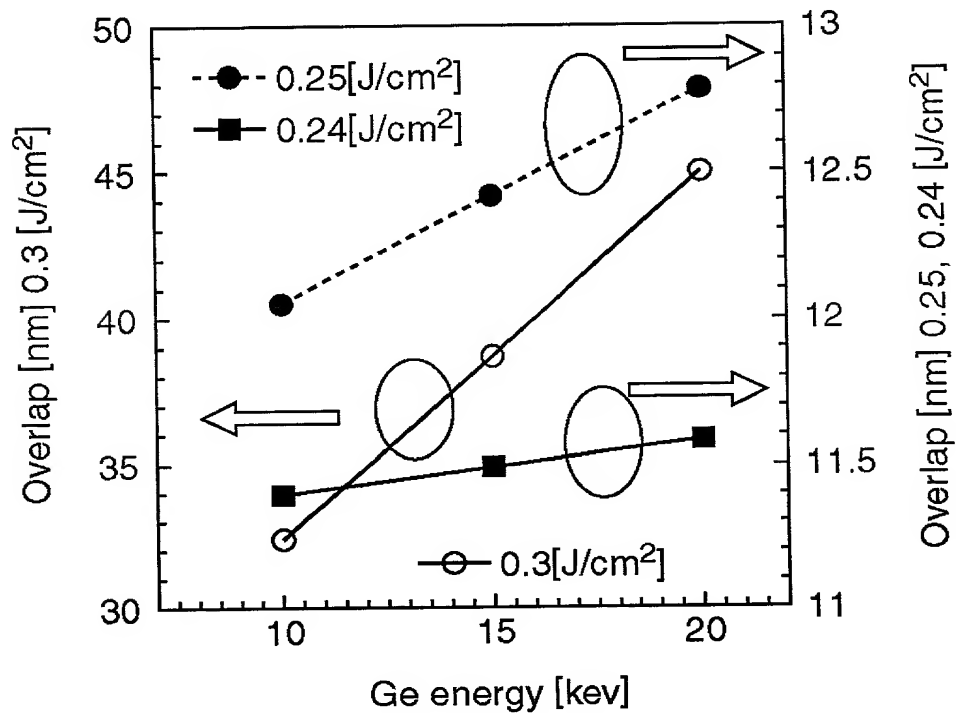


FIG. 5A

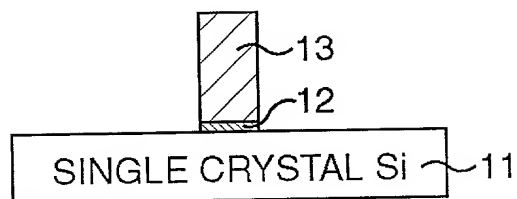


FIG. 5B

A1 Ge⁺ ION IMPLANTATION

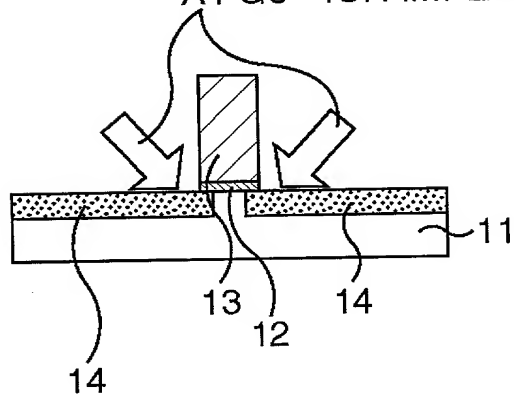


FIG. 5C

A2 B⁺ ION IMPLANTATION

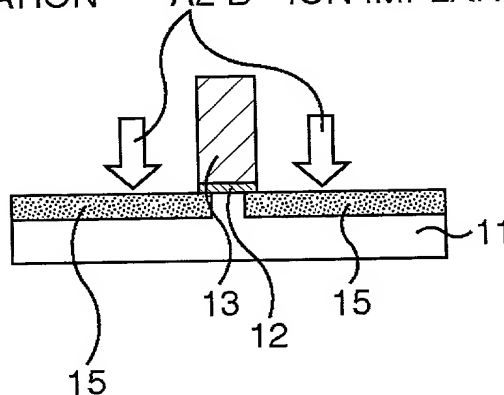


FIG. 5D

A3 Ge⁺ ION IMPLANTATION

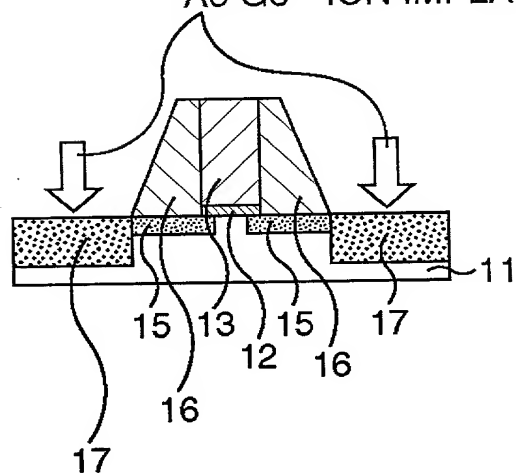


FIG. 5E

A4 B⁺ ION IMPLANTATION

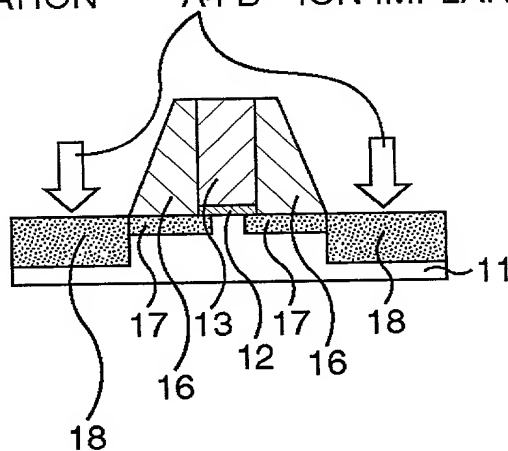


FIG. 6A

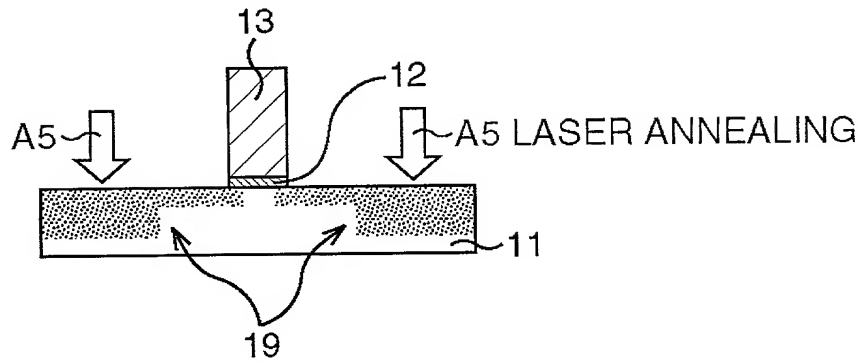


FIG. 6B

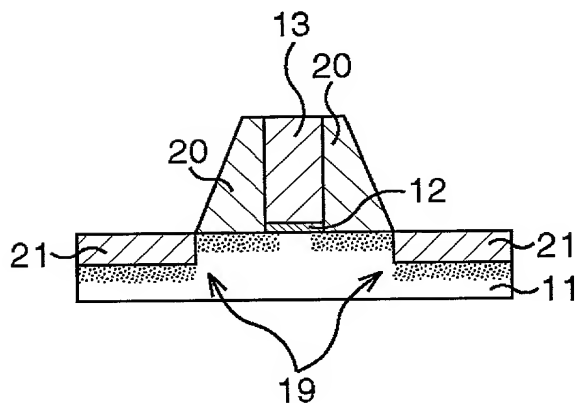


FIG. 6C

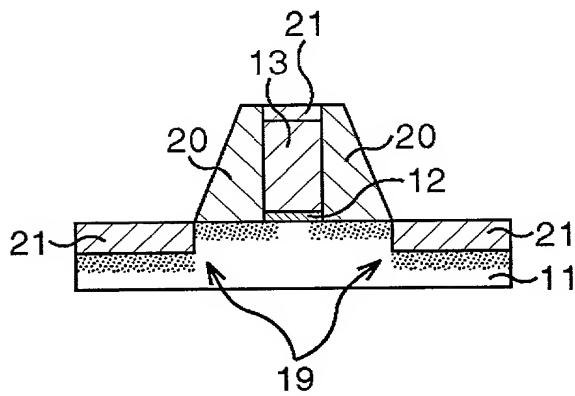


FIG. 7A

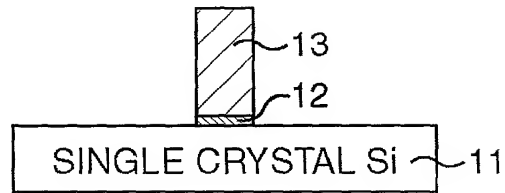


FIG. 7B

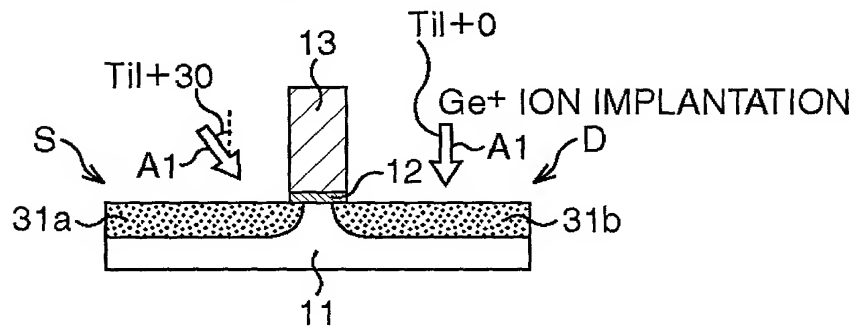


FIG. 7C

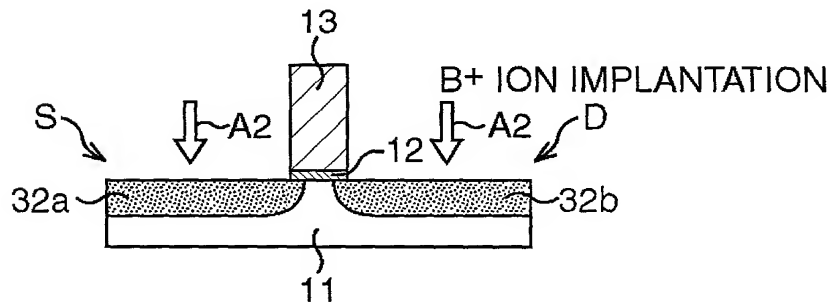


FIG. 7D

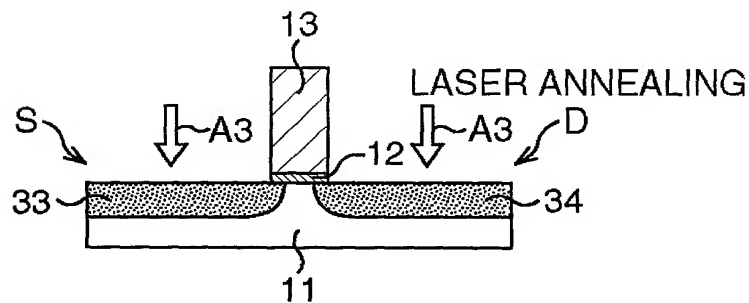


FIG. 8A

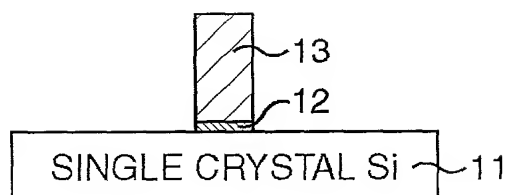


FIG. 8B

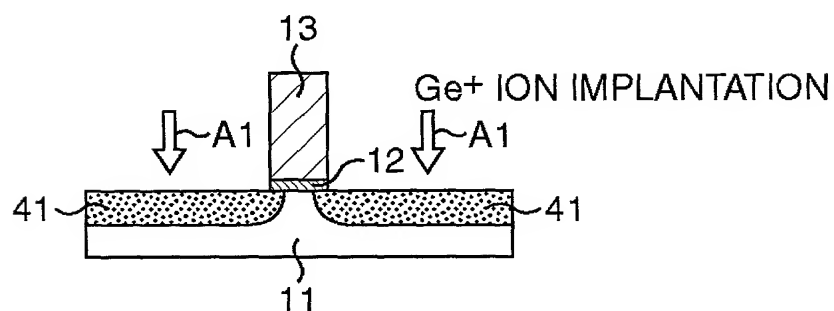


FIG. 8C

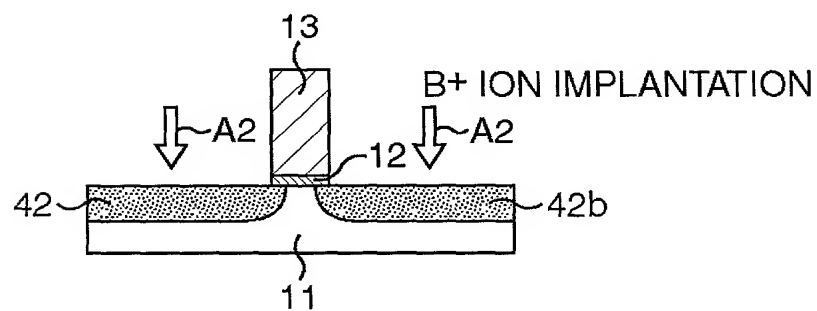


FIG. 8D

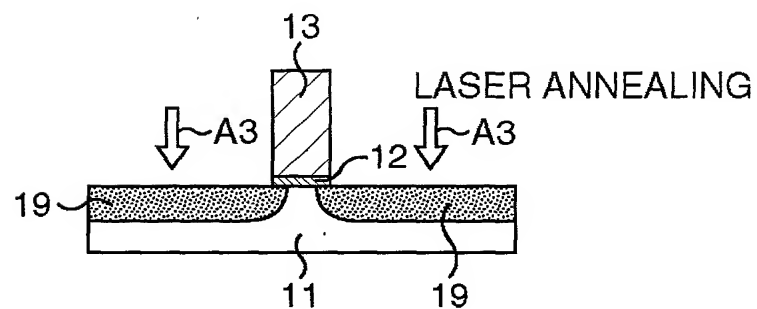


FIG. 9A

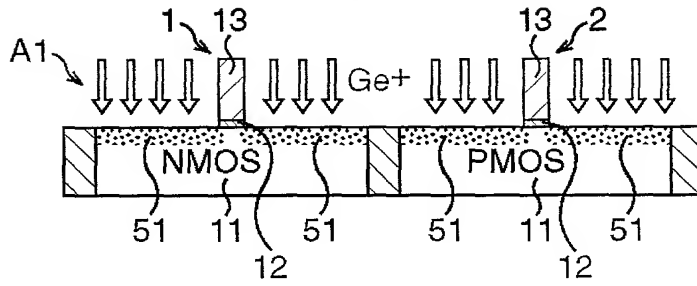


FIG. 9B

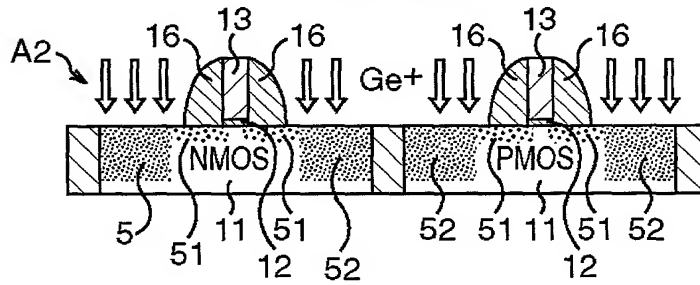


FIG. 9C

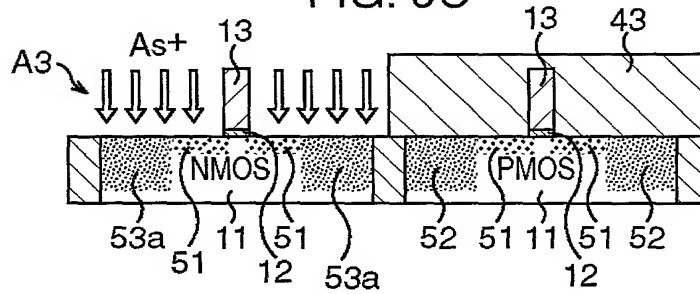


FIG. 9D

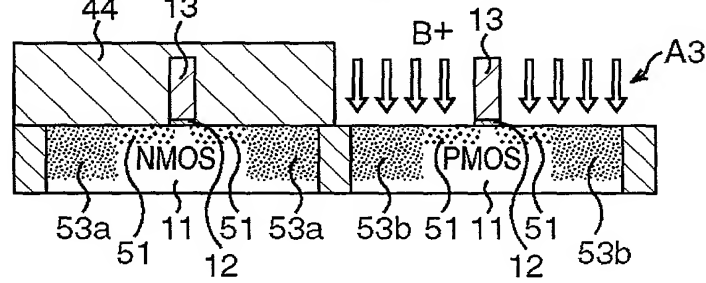


FIG. 9E

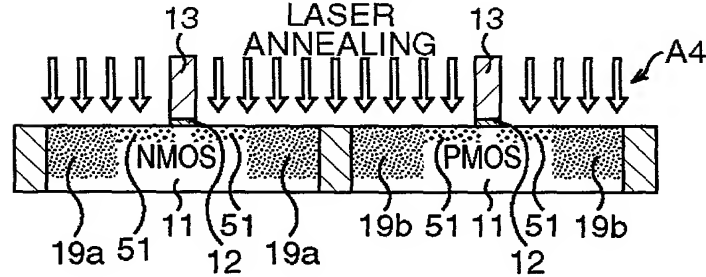


FIG. 10A

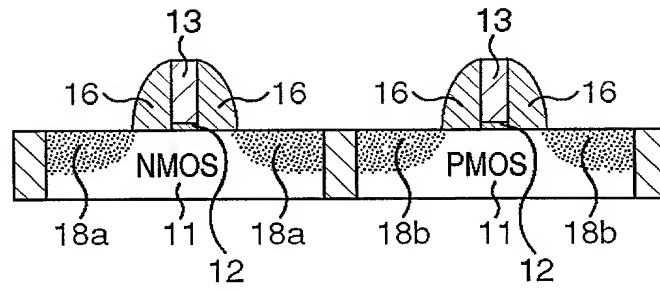


FIG. 10B

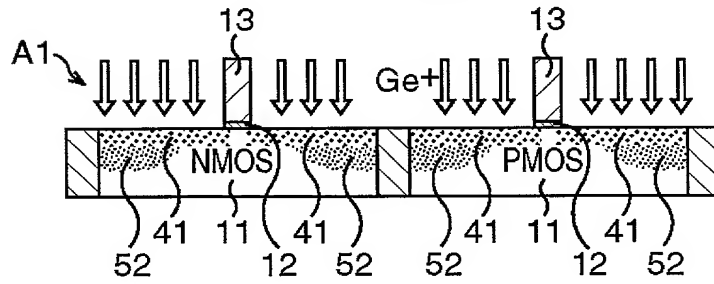


FIG. 10C

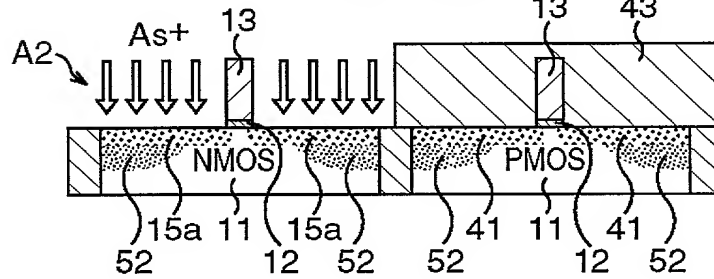


FIG. 10D

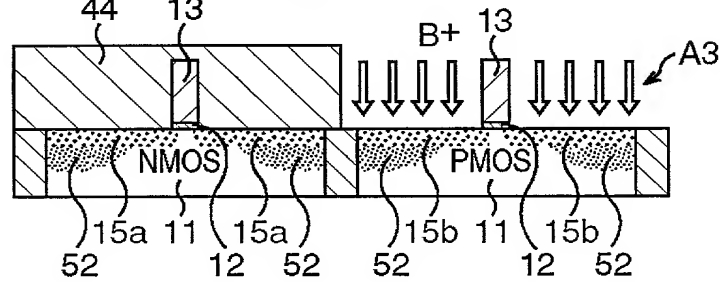


FIG. 10E

